

# **ISC Silicon NPN Power Transistor**

#### **DESCRIPTION**

- Large current capacitance and wide ASO
- Small and slim package making it easy to make 2SD1802/ 2SB1202-used set smaller
- · Low collector-to-emitter saturation voltage
- · Fast switching speed
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

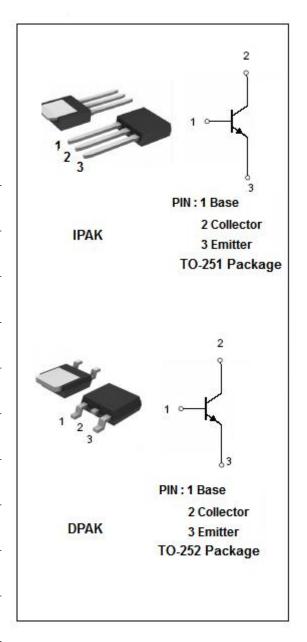


#### **APPLICATIONS**

 Voltage regulators, relay drivers, lamp drivers, electrical equipment

## ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>СВО</sub>	Collector-Base Voltage	60	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	50	V	
V <sub>EBO</sub>	Emitter-Base Voltage	6	V	
lc	Collector Current-Continuous	3	А	
I <sub>CP</sub>	Collector Current-Pulse	6	А	
Pc	Collector Power Dissipation @ T <sub>C</sub> =25°C	15	W	
	Collector Power Dissipation @ Ta=25℃	1.0	W	
Тл	Junction Temperature	150	$^{\circ}$	
T <sub>stg</sub>	T <sub>stg</sub> Storage Temperature Range -55~		$^{\circ}$	





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2SD1802

#### **ELECTRICAL CHARACTERISTICS**

 $T_{\text{C}}$ =25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 2A; I <sub>B</sub> = 100mA			0.5	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> = 2A; I <sub>B</sub> = 100mA			1.2	V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 10uA; I <sub>B</sub> = 0	60			V
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 1mA; I <sub>B</sub> = 0	50			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 10uA; I <sub>C</sub> = 0	6			V
Ісво	Collector Cutoff Current	V <sub>CB</sub> = 40V; I <sub>E</sub> = 0			1	uA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 4V; I <sub>C</sub> = 0			1	uA
h <sub>FE1</sub>	DC Current Gain	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 2V	100		560	
h <sub>FE2</sub>	DC Current Gain	I <sub>C</sub> = 3A; V <sub>CE</sub> = 2V	35			
Сов	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V; f= 1.0MHz		25		pF
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 50mA; V <sub>CE</sub> = 10V		150		MHz

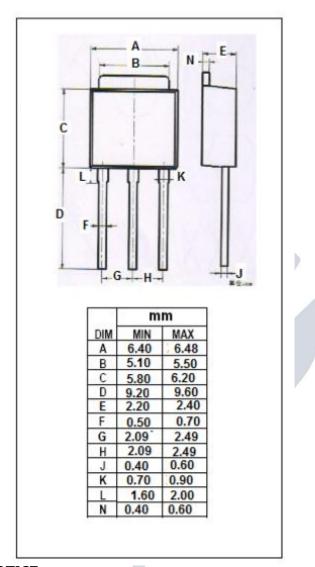
# h<sub>FE1</sub> Classifications

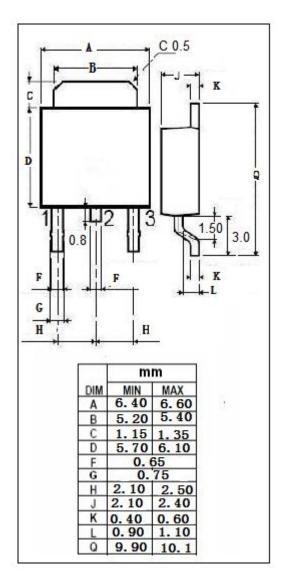
R	S	Т	U
100-200	140-280	200-400	280-560

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#### **Outline Drawing**





## **NOTICE:**

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